

**DL-3149-054****Index Guided AlGaInP Laser Diode****Overview**

DL-3149-054 is 670 nm (Typ.) index guided AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and high operating temperature are achieved by the use of a strained multiple quantum well active layer. DL-3149-054 is suitable for applications such as bar-code scanners, laser pointers and other optical information systems.

Features

- Short wavelength : 670 nm (Typ.)
- High operating temperature : 5 mW at 60°C
- Low threshold current : $I_{th} = 30$ mA (Typ.)
- Small package : 5.6 mm \varnothing

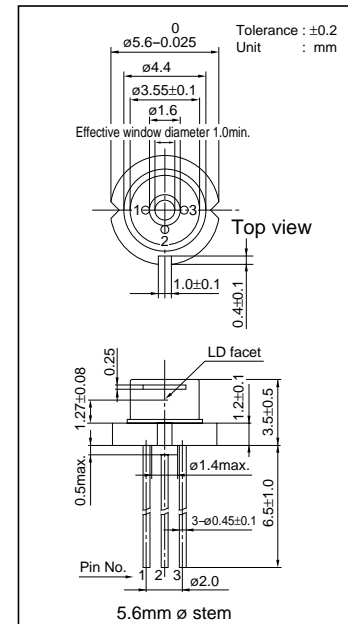
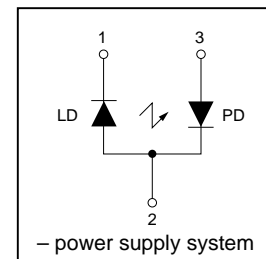
Absolute Maximum Ratings at Tc=25°C

Parameter	Symbol	Ratings	Unit	
Light Output	Po	5	mW	
Reverse Voltage	Laser PIN	VR	2	V
			30	
Operating Temperature	Topr	-10 to +60	°C	
Storage Temperature	Tstg	-40 to +85	°C	

Electrical and Optical Characteristics at Tc=25°C

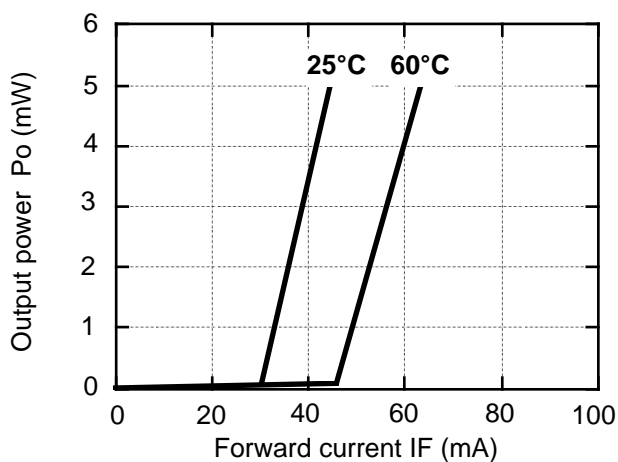
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Threshold Current	Ith	CW	-	30	50	mA	
Operating Current	Iop	Po=5mW	-	45	60	mA	
Operating Voltage	Vop	Po=5mW	-	2.3	2.6	V	
Lasing Wavelength	λ_p	Po=5mW	660	670	680	nm	
Beam \ast) Divergence	Perpendicular	θ_{\perp}	Po=5mW	25	33	40	deg.
	Parallel	$\theta_{//}$	Po=5mW	6	8	10	deg.
Off Axis Angle	Perpendicular	$\Delta\theta_{\perp}$	-	-	-	± 3	deg.
	Parallel	$\Delta\theta_{//}$	-	-	-	± 3	deg.
Differential Efficiency	dPo/dIop	-	0.15	0.3	-	mW/mA	
Monitoring Output Current	Im	Po=5mW	0.4	1.2	2.0	mA	
Astigmatism	As	Po=5mW	-	8	-	μm	

\ast) Full angle at half maximum note : The above product specifications are subject to change without notice.

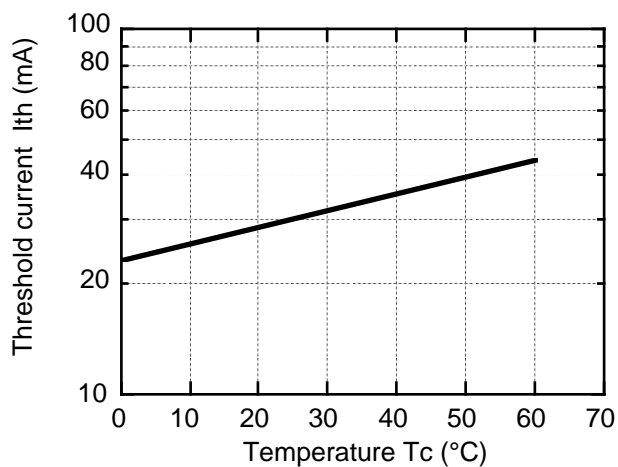
Package Dimensions**Electrical Connection**

Characteristics

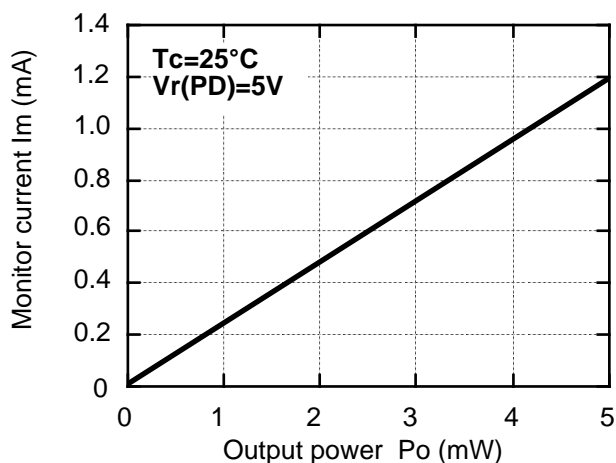
Output power vs. Forward current



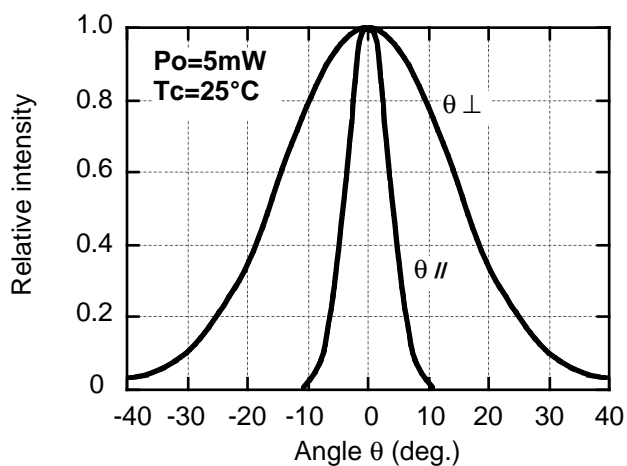
Threshold current vs. Temperature



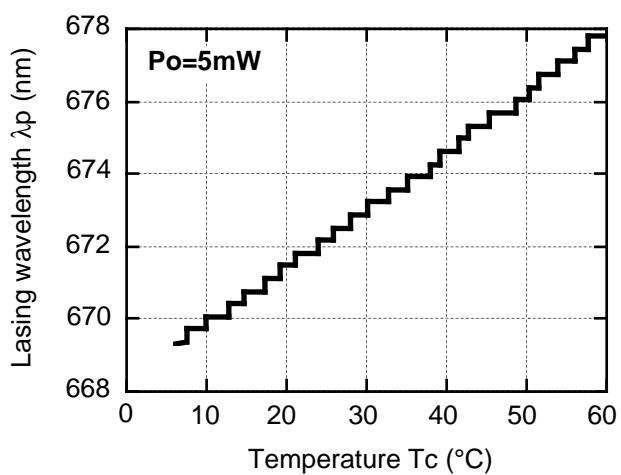
Monitor current vs. Output power



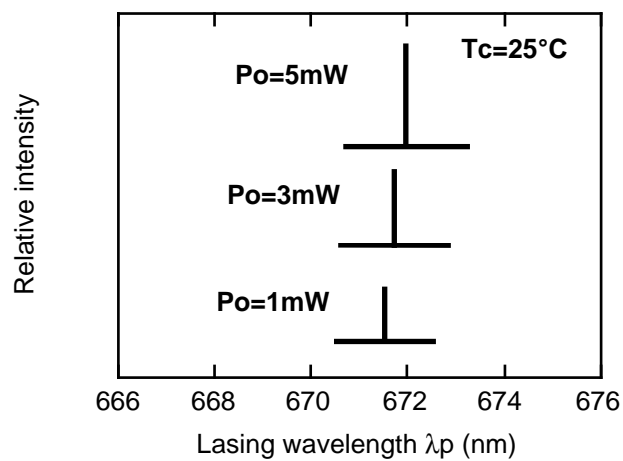
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



 **CAUTION**

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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

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